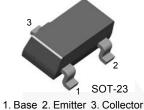


November 2014

# BC817 / BC818 **NPN Epitaxial Silicon Transistor**

## **Features**

- Switching and Amplifier Applications
- · Suitable for AF-Driver Stages and Low Power Output Stages
- · Complement to BC807 / BC808



## Ordering Information(1)

Part Number	Marking	Package	Packing Method	
BC81716MTF	8FA	SOT-23 3L	Tape and Reel	
BC81725MTF	8FB	SOT-23 3L	Tape and Reel	
BC81740MTF	8FC	SOT-23 3L	Tape and Reel	
BC81816MTF	8GA	SOT-23 3L	Tape and Reel	
BC81825MTF	8GB	SOT-23 3L	Tape and Reel	
BC81840MTF	8GC	SOT-23 3L	Tape and Reel	

### Note:

1. Affix "-16,-25,-40" means hFF classification. Affix "-M" means the matte type package. Affix "-TF" means the tape and reel type packing.

## **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at T<sub>A</sub> = 25°C unless otherwise noted.

Symbol	Parameter		Value	Unit
V <sub>CBO</sub> Collector-Base Volta	Callagter Page Voltage	BC817	50	V
	Collector-base voltage	BC818	30	
V <sub>CEO</sub> Coll	Callagter Emitter Voltage	BC817	45	- v
	Collector-Emitter Voltage	BC818	25	
V <sub>EBO</sub>	Emitter-Base Voltage	5	V	
I <sub>C</sub>	Collector Current (DC)	800	mA	
TJ	Junction Temperature	150	°C	
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C	

1

## Thermal Characteristics(1)

Values are at T<sub>A</sub> = 25°C unless otherwise noted.

Symbol	Parameter	Value	Unit
D	Power Dissipation	310	mW
P <sub>D</sub>	Derate Above 25°C	2.48	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	403	°C/W

## Note:

1. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

## Electrical Characteristics(2)

Values are at  $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter		Conditions	Min.	Тур.	Max.	Unit
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	BC817	- 10 m	45			V
		BC818	$I_C = 10 \text{ mA}, I_B = 0$	25			
D\/	Collector-Emitter Breakdown	BC817	$I_{\rm C}$ = 0.1 mA, $V_{\rm BE}$ = 0	50			V
BV <sub>CES</sub>	Voltage	BC818		30			
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage		I <sub>E</sub> = 0.1 mA, I <sub>C</sub> = 0	5			V
I <sub>CES</sub>	Collector Cut-Off Current		V <sub>CE</sub> = 25 V, V <sub>BE</sub> = 0			100	nA
I <sub>EBO</sub>	Emitter Cut-Off Current		$V_{EB} = 4 \text{ V}, I_{C} = 0$			100	nA
h <sub>FE1</sub>	h <sub>FE1</sub> DC Current Gain		$V_{CE} = 1 \text{ V, } I_{C} = 100 \text{ mA}$	100		630	
h <sub>FE2</sub>			$V_{CE} = 1 \text{ V, } I_{C} = 300 \text{ mA}$	60			
V <sub>CE</sub> (sat)	) Collector-Emitter Saturation Voltage		I <sub>C</sub> = 500 mA, I <sub>B</sub> = 50 mA			0.7	V
V <sub>BE</sub> (on)	) Base-Emitter On Voltage		$V_{CE} = 1 \text{ V, } I_{C} = 300 \text{ mA}$			1.2	V
f <sub>T</sub>	Current Gain Bandwidth Product		V <sub>CE</sub> = 5 V, I <sub>C</sub> = 10 mA, f = 50 MHz		100		MHz
C <sub>ob</sub>	Output Capacitance		V <sub>CB</sub> = 10 V, f = 1 MHz			12	pF

#### Note:

2. Pulse test: pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2%

## **h**<sub>FE</sub> Classification

Classification	16	25	40
h <sub>FE1</sub>	100 ~ 250	160 ~ 400	250 ~ 630
h <sub>FE2</sub>	60 ~	100 ~	170 ~

## **Typical Performance Characteristics**

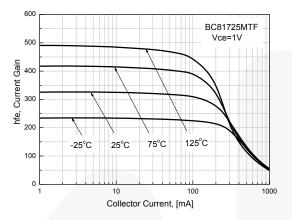


Figure 1. DC Current Gain

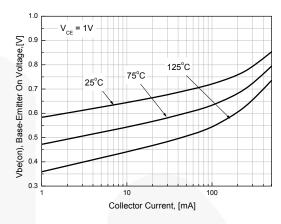


Figure 2. Base-Emitter On Voltage

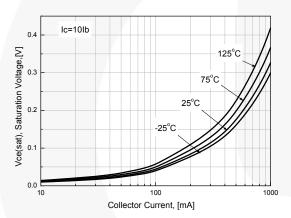


Figure 3. Collector-Emitter Saturation Voltage

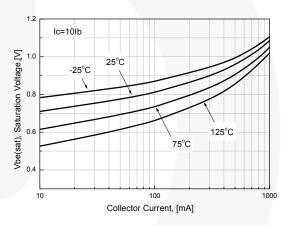


Figure 4. Base-Emitter Saturation Voltage

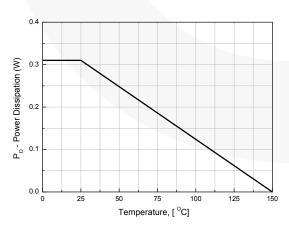
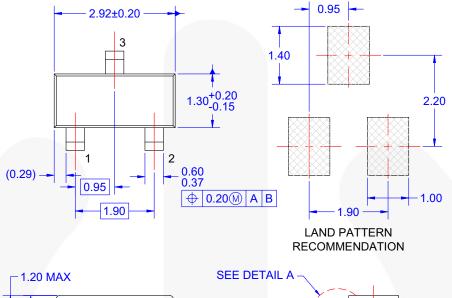
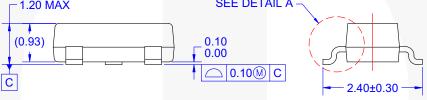
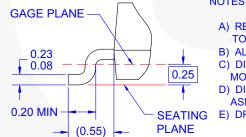


Figure 5. Power Dissipation vs Ambient Temperature

## **Physical Dimensions**







- NOTES: UNLESS OTHERWISE SPECIFIED
  - A) REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE H.
  - B) ALL DIMENSIONS ARE IN MILLIMETERS.
  - C) DIMENSIONS ARE INCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
  - D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M 1994.
- SEATING E) DRAWING FILE NAME: MA03DREV10

DETAIL A

Figure 6. 3-LEAD, SOT23, JEDEC TO-236, LOW PROFILE





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Rev. 172